

L Number	Hits	Search Text	DB	Time stamp
-	529	(257/72).CCLS.	USPAT	2004/01/29 17:33
-	6794	(scan\$4 and data) near2 (line\$1)	USPAT	2001/10/16 10:28
-	58	((scan\$4 and data) near2 (line\$1)) and (("257/72").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 14:18
-	131	((((scan\$4 and data) (gate\$1 and drain\$1)) near2 (line\$1 wir\$4)) and (("257/72").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 10:42
-	102	(pixel near electrode\$1) and (((scan\$4 and data) (gate\$1 and drain\$1)) near2 (line\$1 wir\$4)) and (("257/72").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 17:32
-	102	((pixel near electrode\$1) and (((scan\$4 and data) (gate\$1 and drain\$1)) near2 (line\$1 wir\$4)) and (("257/72").CCLS.))) and (transistor\$1 gate\$1 near electrode\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 15:41
-	2	monocrystal\$4 near silicon and (((pixel near electrode\$1) and (((scan\$4 and data) (gate\$1 and drain\$1)) near2 (line\$1 wir\$4)) and (("257/72").CCLS.))) and (transistor\$1 gate\$1 near electrode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 15:44
-	2	insulat\$5 near substrate same mono\$11 near3 silicon and (("257/72").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 15:51
-	4	insulat\$5 near substrate and mono\$11 near3 silicon and (("257/72").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 15:54
-	2	(insulat\$5 near substrate and mono\$11 near3 silicon and (("257/72").CCLS.)) not (insulat\$5 near substrate same mono\$11 near3 silicon and (("257/72").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 15:53
-	3	insulat\$5 near substrate and mono\$11 near3 silicon and lcd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 15:58
-	2	(insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and (("257/72").CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 15:56
-	2	insulat\$5 near substrate and mono adj crystal\$5 near3 silicon and lcd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:00

-	0	(insulat\$5 near substrate and mono adj crystal\$5 near3 silicon and lcd) not (((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:00
-	5	(glass quartz insulat\$4) near5 substrate and mono adj crystal\$5 near3 silicon and lcd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:03
-	3	((glass quartz insulat\$4) near5 substrate and mono adj crystal\$5 near3 silicon and lcd) not (((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:04
-	201	(glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 silicon and lcd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:04
-	4021	(glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:04
-	20	(glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 silicon and lcd and ("257/72").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:21
-	9	104not (((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (((glass quartz insulat\$4) near5 substrate and mono adj crystal\$5 near3 silicon and lcd) not (((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:05

-	20	((glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 silicon and lcd and ("257/72").CCLS.) not (((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (((glass quartz insulat\$4) near5 substrate and mono adj crystal\$5 near3 silicon and lcd) not (((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:22
-	4	(glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 semiconductor and lcd and ("257/72").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:23
-	1	((glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 semiconductor and lcd and ("257/72").CCLS.) not (((glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 silicon and lcd and ("257/72").CCLS.) ((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (((glass quartz insulat\$4) near5 substrate and mono adj crystal\$5 near3 silicon and lcd) not (((insulat\$5 near substrate and mono\$11 near3 silicon and lcd) not (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and lcd) ((insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.) not (insulat\$5 near substrate same mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.))) (insulat\$5 near substrate and mono\$11 near3 silicon and ("257/72").CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:22
-	0	lcd and ((glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 island)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:24
-	0	("257/72").CCLS.) and ((glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 island)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:24

-	121	(glass quartz insulat\$4) near5 substrate and (mono adj crystal\$5 monocrystal\$5) near3 island	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:29
-	728	(257/72).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/16 16:44
-	150	(257/72).CCLS.	JPO	2001/10/16 16:44
-	11	((scan\$4 and data) near2 (line\$1)) and (("257/72").CCLS.) and @pd>=20011016	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 17:20
-	9	gate\$1 near2 length\$1 with parallel with data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:25
-	0	("L.sub.g") with parallel with data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:29
-	1	("G.sub.l") with parallel with data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:30
-	85	((scan\$4 and data) near2 (line\$1)) and (("257/72").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:03
-	5	KAWATA-HIROTAKA	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:49
-	642	(257/72).CCLS.	USPAT	2002/10/22 15:54
-	5	(monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:18
-	0	monocrystalline adj silicon with semiconductor adj layer with preferably	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:57
-	1	monocrystalline adj silicon with semiconductor adj layer with prefer\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:58
-	1	monocrystalline adj silicon with semiconductor adj layer\$1 with prefer\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:18

-	139	single adj crystalline adj silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:18
-	396	(monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 18:01
-	3	(single adj crystalline adj silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:19
-	9	((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:20
-	1	(((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) not (((single adj crystalline adj silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:20
-	4	mono adj crystalline near2 silicon with semiconductor adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:20
-	186	monocrystalline adj silicon with semiconductor adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:48
-	33977	(monocrystalline adj silicon with semiconductor adj layer) and tft thin adj film adj transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:50
-	33	(monocrystalline adj silicon with semiconductor adj layer) and (tft thin adj film adj transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 16:50
-	1056	(monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:58
-	7	((monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1) and ((257/72).CCLS.) not (((single adj crystalline adj silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) (((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59

-	47	(monocrystal\$4) near2 silicon with semiconductor adj film\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59
-	630	156and ((257/72).CCLS.) not (((single adj crystalline adj silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) (((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.)) ((monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59
-	0	((monocrystal\$4) near2 silicon with semiconductor adj film\$1) and ((257/72).CCLS.) not (((single adj crystalline adj silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) (((monocrystalline single adj crystalline) near2 silicon with semiconductor adj layer\$1) and ((257/72).CCLS.)) ((monocrystalline adj silicon with semiconductor adj layer) and ((257/72).CCLS.)) ((monocrystal\$4 single adj crystal\$4) near2 silicon with semiconductor adj layer\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:59
-	6	(monocrystal\$4) near2 (Si "si") with semiconductor adj film\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 18:00
-	293	(monocrystal\$4) near2 silicon with semiconductor adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 18:01
-	51	(monocrystal\$4) near2 silicon with semiconductor adj layer\$1 and (tft\$1 thin adj film adj transistor\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 13:46
-	1036	(257/72).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 13:47
-	0	((monocrystal\$4) near2 silicon with semiconductor adj layer\$1 and (tft\$1 thin adj film adj transistor\$1) and @pd>=20021022) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 13:47
-	7	(monocrystal\$4) near2 silicon with semiconductor adj layer\$1 and (tft\$1 thin adj film adj transistor\$1) and @pd>=20021022	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 13:47
-	23	((scan\$4 and data) near2 (line\$1)) and (("257/72").CCLS.) and @pd>=20030820	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 17:21

-	5652	(scan scanning) near line with (gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 17:33
-	1297	(257/72).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 17:33
-	164	((scan scanning) near line with (gate electrode)) and ((257/72).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/29 17:33
-	149	((((scan scanning) near line with (gate electrode)) and ((257/72).CCLS.)) not (((scan\$4 and data) near2 (line\$1)) and (("257/72").CCLS.) and @pd>=20030820)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/30 12:11
-	2	("6297862").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/30 12:12
-	0	wo-0916168-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/30 12:12
-	2	wo-9816868-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/30 12:13
-	27	murade	JPO	2004/01/30 12:14
-	0	6573955.URPN.	USPAT	2004/01/30 13:59
-	14	("4759610" "5337173" "5432625" "5517342" "5680186" "5724107" "5744821" "5745194" "5781261" "5822027" "5936685" "5966193" "6259200" "6323918").PN.	USPAT	2004/01/30 14:00